



100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D T _C = +25°C
100V	13.5mΩ @ V _{GS} = 10V	42A
	18mΩ @ V _{GS} = 6.0V	36A
	23.5mΩ @ V _{GS} = 4.5V	32A

Description and Applications

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

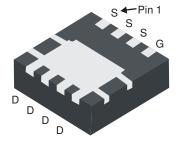
- · Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low R_{DS(ON)} Ensures On State Losses Are Minimized
- Excellent Q_{qd x} R_{DS (ON)} Product (FOM)
- Advanced Technology for DC/DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of The Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% UIS (Avalanche) Rated
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

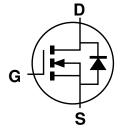
- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.008 grams (Approximate)



Bottom View



Top View



Equivalent Circuit

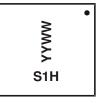
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT10H015LFG-7	PowerDI3333-8	2,000/Tape & Reel
DMT10H015LFG-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



S1H = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 17 = 2017) WW = Week Code (01 to 53)



Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note EV V 10V	$T_A = +25$ °C $T_A = +70$ °C	I _D	10 8.0	Α
Continuous Drain Current (Note 5) V _{GS} = 10V	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I _D	42 26	А
Maximum Continuous Body Diode Forward Current (Note 5)	Is	1.5	Α	
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I _{DM}	75	Α	
Avalanche Current (L = 3mH)		I _{AS}	7.5	Α
Avalanche Energy (L = 3mH)		E _{AS}	85	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

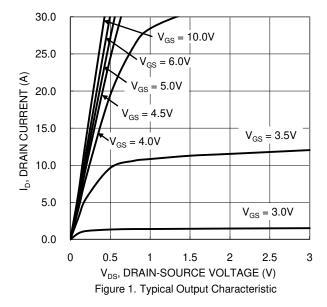
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P_{D}	2.0	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ hetaJA}$	61	°C/W	
Total Power Dissipation	$T_C = +25^{\circ}C$	P _D	35	W
Thermal Resistance, Junction to Case		$R_{ hetaJC}$	3.5	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV_{DSS}	100		_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	1	1	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(TH)}	1.4	2.0	3.5	٧	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
		I	10.8	13.5		$V_{GS} = 10V, I_D = 20A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	I	13.3	18	mΩ	$V_{GS} = 6.0V, I_D = 20A$	
		1	17.9	23.5		$V_{GS} = 4.5V, I_D = 20A$	
Diode Forward Voltage	V_{SD}	I	0.9	1.3	٧	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	Ciss	-	1,871	_		$V_{DS} = 50V$, $V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss	1	261	_	pF		
Reverse Transfer Capacitance	C _{rss}	l	6.9	_			
Gate Resistance	Rg	I	0.75	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Q_g	l	33.3	_		V 50V L 10A	
Gate-Source Charge	Q_{gs}	I	6.9	_	nC	$V_{DD} = 50V, I_D = 10A,$ $V_{GS} = 10V$	
Gate-Drain Charge	Q_{gd}	l	5.1	_		VGS ≡ 10V	
Turn-On Delay Time	t _{D(ON)}		6.5	_			
Turn-On Rise Time	t _R		7.0	_	$V_{DD} = 50V, V_{GS} = 10V,$		
Turn-Off Delay Time	t _{D(OFF)}	_	19.7	_	115	$I_D = 10A$, $R_G = 6\Omega$	
Turn-Off Fall Time	t _F	_	8.1	_			
Reverse Recovery Time	t _{RR}	-	37.9	_	ns	L 104 di/dt 1004/up	
Reverse Recovery Charge	Q _{RR}	_	51.9	_	nC	$I_F = 10A$, di/dt = 100A/ μ s	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.6. Short duration pulse test used to minimize self-heating effect.7. Guaranteed by design. Not subject to product testing.





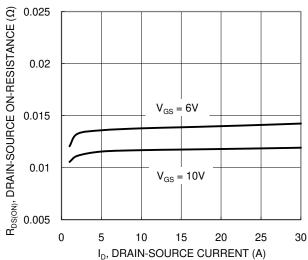


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

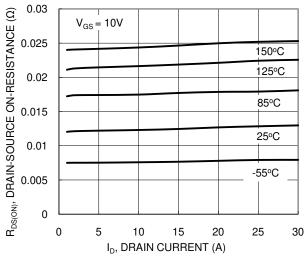
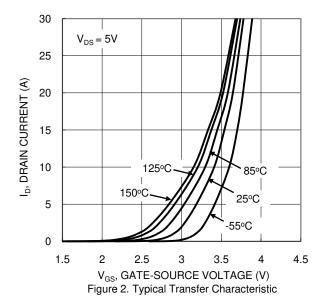


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



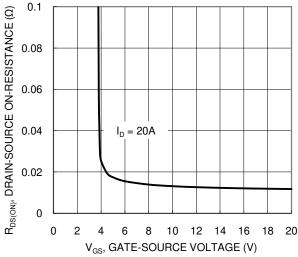


Figure 4. Typical Transfer Characteristic

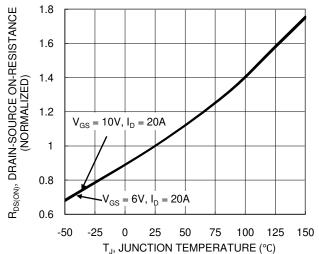


Figure 6. On-Resistance Variation with Junction Temperature





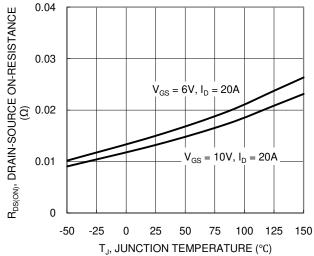


Figure 7. On-Resistance Variation with Junction Temperature

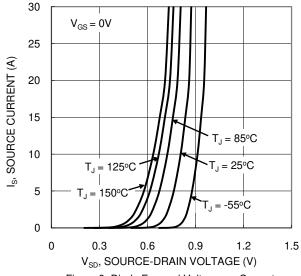


Figure 9. Diode Forward Voltage vs. Current

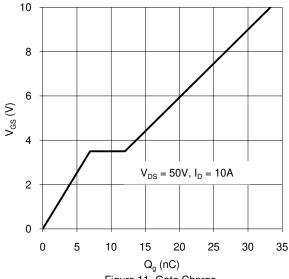


Figure 11. Gate Charge

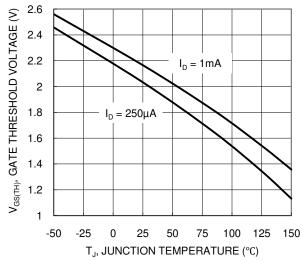
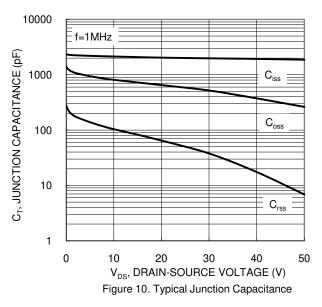
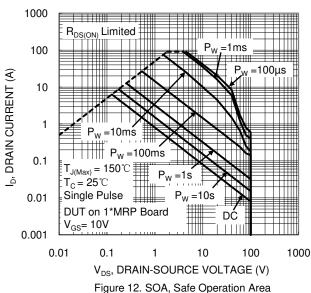


Figure 8. Gate Threshold Variation vs. Junction Temperature







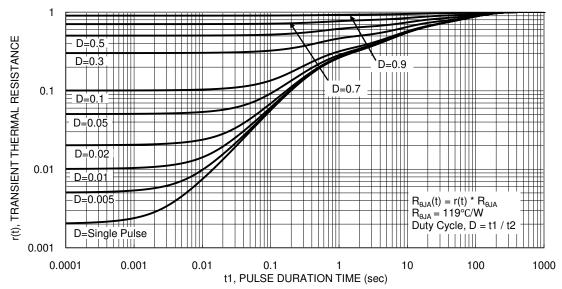


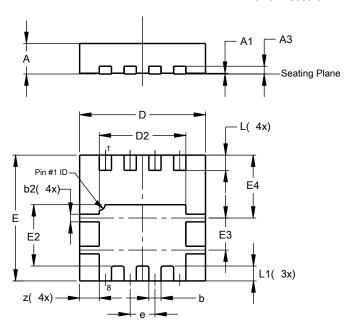
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

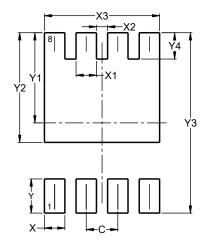


PowerDI3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	1	1	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
E	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
е	-	-	0.65		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z	_	_	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
С	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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